Magnetization process and magnetic anisotropy of $Ga_{1-x}Mn_xAs$ on GaAs (311)A substrate

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We have studied magnetization processes and magnetic anisotropy of $Ga_{0.94}Mn_{0.06}As$ thin film grown by low-temperature molecular beam epitaxy on GaAs (311)A substrates by means of superconducting quantum interference device (SQUID) and magnetooptic microscopy. The magnetization curve obtained by SQUID are explained phenomenologically using two main contributions to the magnetic anisotropy: a cubic magnetocrystaline anisotropy with easy <001> axes, and an effective uniaxial magnetic anisotropy with hard axis along [311] caused by the epitaxial compressive strain from the substrate. We find the uniaxial anisotropy constant to depend linearly on M_S^2 and the cubic anisotropy constant to follow M_S^4 (here M_S is saturation magnetization), confirming the validity of the single domain model used to describe magnetization rotations in this material. Our results are in agreement with ferromagnetic resonance data¹ and expectation of the p-d Zener model of the carried mediated ferromagnetism².

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- 2. T. Dietl, H. Ohno, F. Matsukura, Phys. Rev. B, 63, 195205 (2001).

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 $9.7~\mathrm{cm}$